

Features

- Low conduction loss due to low V_F
- Extremely low switching loss by tiny Q_C
- Highly rugged due to better surge current
- Industrial standard quality and reliability
- RoHS compliant with Halogen-free

HF

Applications

- UPS
- Power Inverter
- High performance SMPS
- Power factor correction

Mechanical Data

- Case: TO-252
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

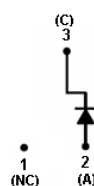
Key performance parameters

Type	GSC2D1065D/DS/DN
V_{DC}	650V
I_F @ 158°C	10A
Q_C @400V	37nC
T_J	175°C

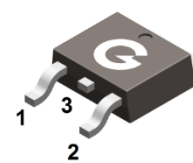


GSC2D1065D

GSC2D1065DS



GSC2D1065DN



TO-252

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GSC2D1065D	TO-252	80 pcs / Tube or 2500 pcs / Tape & Reel	GSC2D1065D
GSC2D1065DS	TO-252	80 pcs / Tube or 2500 pcs / Tape & Reel	GSC2D1065DS
GSC2D1065DN	TO-252	80 pcs / Tube or 2500 pcs / Tape & Reel	GSC2D1065DN

Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	650	V
Surge Peak Reverse Voltage	V_{RSM}	650	V
DC Peak Reverse Voltage	V_R	650	V
Continuous Forward Current ($T_C = 25^\circ\text{C}$)	I_F	30	A
Continuous Forward Current ($T_C = 135^\circ\text{C}$)		15	
Continuous Forward Current ($T_C = 158^\circ\text{C}$)		10	
Non-Repetitive Forward Surge Current (10ms single half sine-wave, $T_C = 25^\circ\text{C}$)	I_{FSM}	80	A
Non-Repetitive Forward Surge Current (10ms single half sine-wave, $T_C = 110^\circ\text{C}$)		70	
Repetitive Peak Forward Surge Current (10ms half sine-wave, $T_C = 25^\circ\text{C}$)	I_{FRM}	45	A
Repetitive Peak Forward Surge Current (10ms half sine-wave, $T_C = 110^\circ\text{C}$)		27	
i^2dt value (10ms single half sine-wave, $T_C = 25^\circ\text{C}$)	$\int i^2 dt$	31.7	A^2s
i^2dt value (10ms single half sine-wave, $T_C = 110^\circ\text{C}$)		24.3	

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	75	W
Power Dissipation ($T_C = 110^\circ\text{C}$)		32	
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	2	$^\circ\text{C/W}$
Operating junction Temperature	T_J	-55 ~ +175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +175	$^\circ\text{C}$

Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 100\mu\text{A}$	650	-	-	V
Forward Voltage	V_F	$I_F = 10\text{A}, T_J = 25^\circ\text{C}$	-	1.3	1.5	V
		$I_F = 10\text{A}, T_J = 175^\circ\text{C}$	-	1.5	-	
Maximum Peak Reverse Current	I_R	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$	-	0.2	25	μA
		$V_R = 650\text{V}, T_J = 175^\circ\text{C}$	-	5	100	
Total Capacitive Charge	Q_C	$V_R = 400\text{V}, T_J = 25^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V)dV$	-	37	-	nC
Total Capacitance	C_J	$V_R = 0\text{V}, f = 1\text{MHz}$	-	800	-	pF
		$V_R = 200\text{V}, f = 1\text{MHz}$	-	70	-	
		$V_R = 400\text{V}, f = 1\text{MHz}$	-	51	-	

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

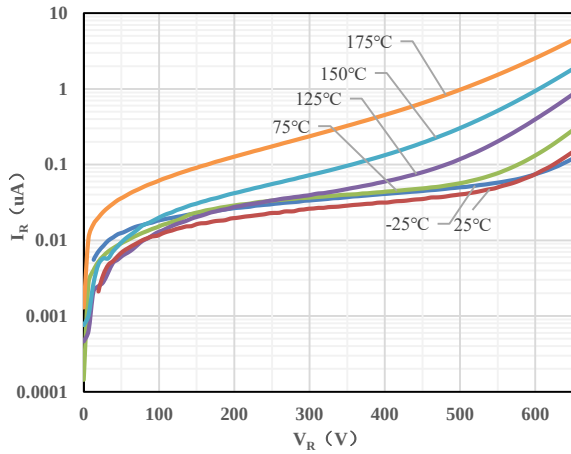


Fig 1 Typical Reverse Characteristic

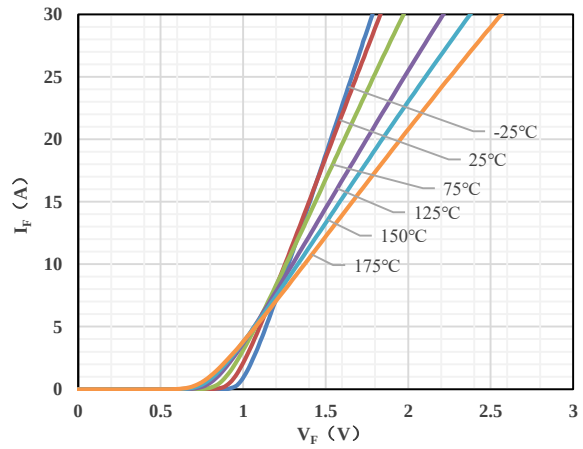


Fig 2 Typical Forward Characteristics

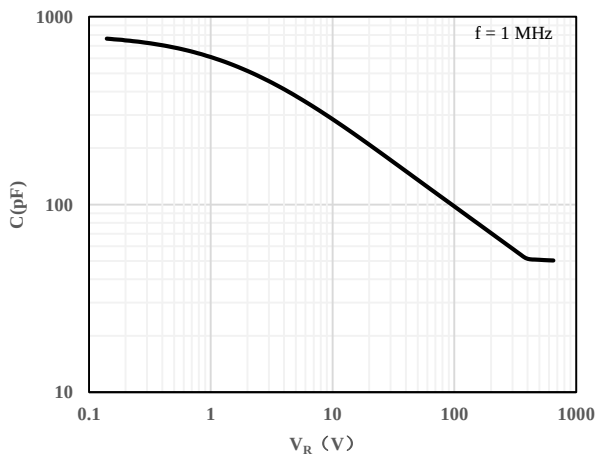


Fig 3 Capacitance vs. Reverse Voltage

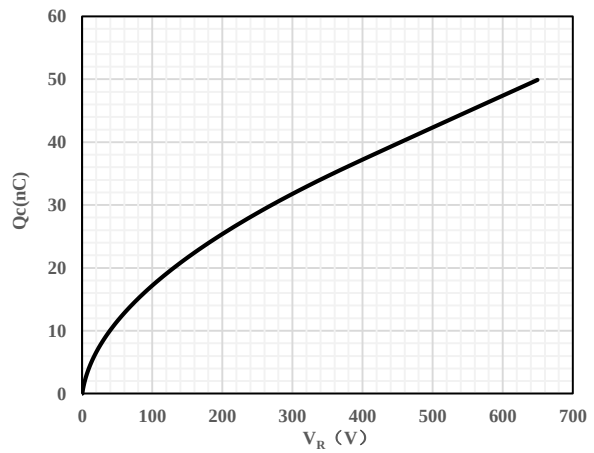


Fig 4 Reverse Charge vs. Reverse Voltage

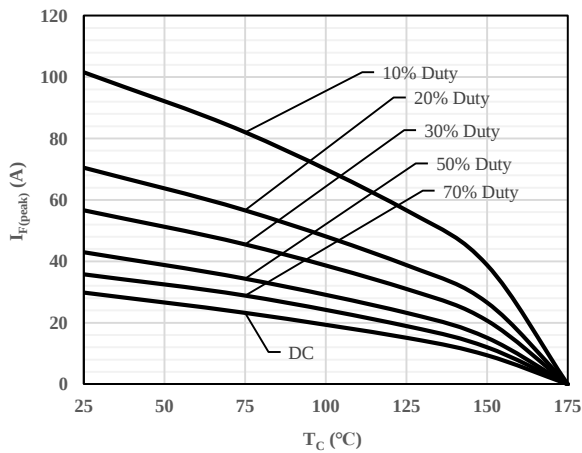


Fig 5 Current Derating

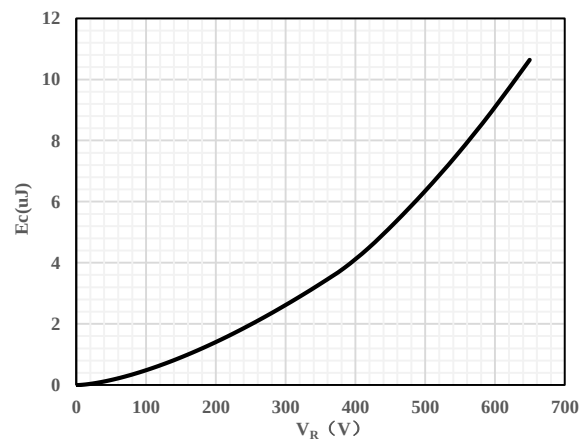
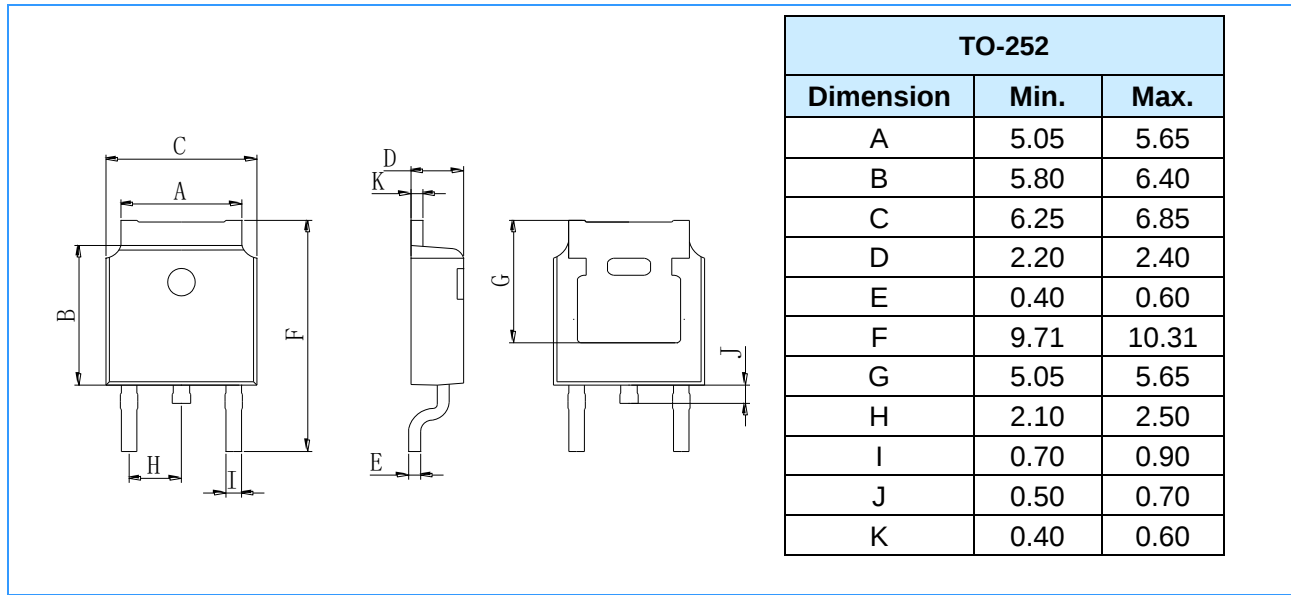


Fig 6 Typical Capacitance Stored Energy

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)

